Supplementary Materials

Evolution of Nanopores in Hexagonal Boron Nitride

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TEM Characterization of Monolayer Hexagonal Boron Nitride (h-BN) Membrane:

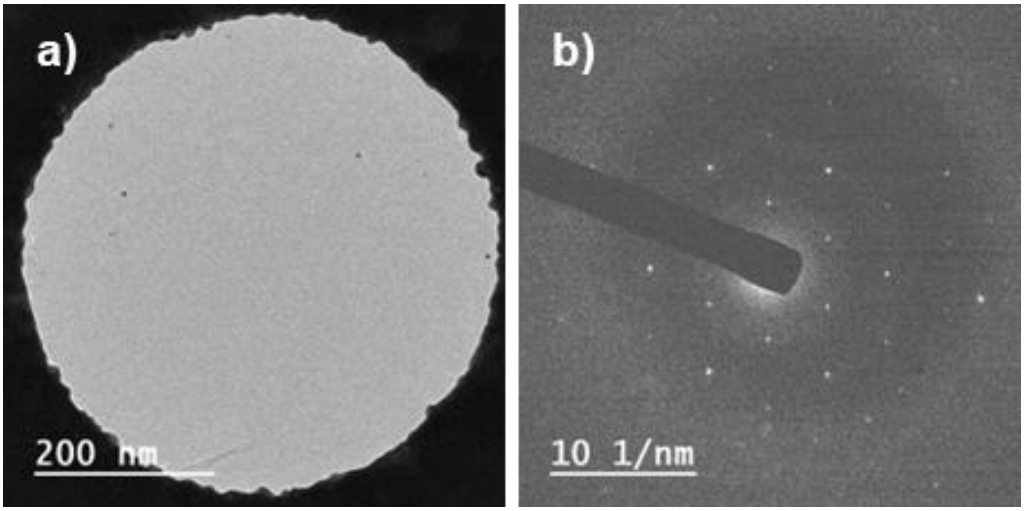

Figure S1, a) TEM image of a monolayer h-BN membrane transferred onto a holey TEM grid through a wet transfer process. b) Selected area electron diffraction (SEAD) of the monolayer h-BN studied in this work.

Time Series of Defects form in Bernal Stacked Mulatilayer h-BN:

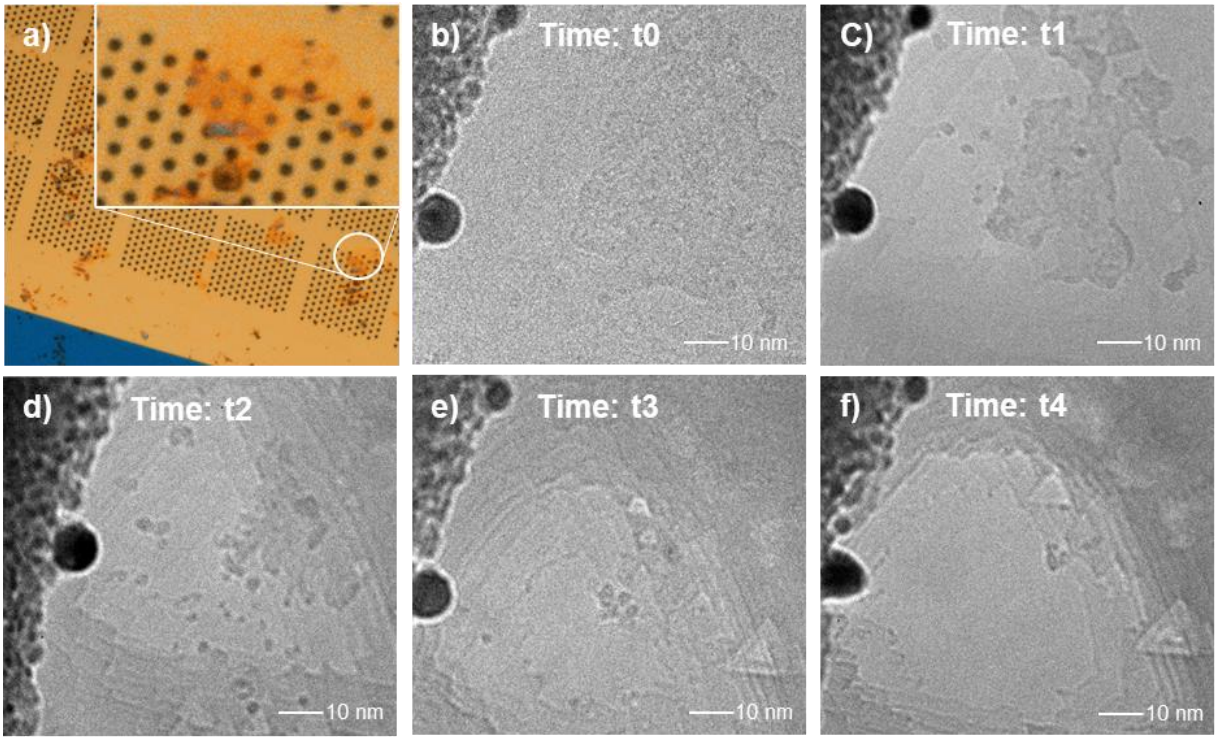

Figure S2, a) Multilayer Bernal stacked h-BN transferred onto a holey TEM grid through a wet transfer process. The membrane is ~10nm. b) TEM image of the initial condication (Time: t0) of the membrane. c-f) TEM time series (Time: t1 to t4) showing the formation of nanopores and stripping of layers under an electron beam with a beam current of ~40 A/cm^2. The time interval between tn and tn+1 is approximately 30 minutes. The beam is expended for imaging with a beam current of ~3 A/cm^2.